## MC3488A

## Dual EIA-423/EIA-232D Line Driver

The MC3488A dual is single-ended line driver has been designed to satisfy the requirements of EIA standards EIA-423 and EIA-232D, as well as CCITT X.26, X. 28 and Federal Standard FIDS1030. It is suitable for use where signal wave shaping is desired and the output load resistance is greater than $450 \Omega$. Output slew rates are adjustable from $1.0 \mu \mathrm{~s}$ to $100 \mu \mathrm{~s}$ by a single external resistor. Output level and slew rate are insensitive to power supply variations. Input undershoot diodes limit transients below ground and output current limiting is provided in both output states.

The MC3488A has a standard 1.5 V input logic threshold for TTL or NMOS compatibility.

## Features

- PNP Buffered Inputs to Minimize Input Loading
- Short Circuit Protection
- Adjustable Slew Rate Limiting
- MC3488A Equivalent to 9636A
- Output Levels and Slew Rates are Insensitive to Power Supply Voltages
- No External Blocking Diode Required for $\mathrm{V}_{\mathrm{EE}}$ Supply
- Second Source $\mu$ A9636A
- Pb -Free Packages are Available


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## MARKING DIAGRAMS



PDIP-8 P1 SUFFIX CASE 626


A $\quad=$ Assembly Location
$\mathrm{L}, \mathrm{WL}=$ Wafer Lot
Y, YY = Year
$W, W W=$ Work Week

- or G = Pb-Free Package
(Note: Microdot may be in either location)

PIN CONNECTIONS


ORDERING INFORMATION
See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.


Figure 1. Simplified Application

MAXIMUM RATINGS (Note 1)

| Rating | Symbol | Value | Unit |
| :--- | :---: | :---: | :---: |
| Power Supply Voltages | $\mathrm{V}_{\mathrm{CC}}$ | +15 | V |
|  | $\mathrm{~V}_{\mathrm{EE}}$ | -15 |  |
| Output Current | Source | $\mathrm{I}_{\mathrm{O}}$ | +150 |
|  | Sink | $\mathrm{I}_{\mathrm{O}}-$ | mA |
| Operating Ambient Temperature | $\mathrm{T}_{\mathrm{A}}$ | 0 to +70 | ${ }^{\circ} \mathrm{C}$ |
| Junction Temperature Range | $\mathrm{T}_{\mathrm{J}}$ | 150 | ${ }^{\circ} \mathrm{C}$ |
| Storage Temperature Range | $\mathrm{T}_{\text {stg }}$ | -65 to +150 | ${ }^{\circ} \mathrm{C}$ |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Devices should not be operated at these values. The "Electrical Characteristics" provide conditions for actual device operation.

## RECOMMENDED OPERATING CONDITIONS

| Characteristic | Symbol | Min | Typ | Max | Unit |
| :--- | :---: | :---: | :---: | :---: | :---: |
| Power Supply Voltages | $\mathrm{V}_{\mathrm{CC}}$ | 10.8 | 12 | 13.2 | V |
|  | $\mathrm{~V}_{\mathrm{EE}}$ | -13.2 | -12 | -10.8 |  |
| Operating Temperature Range | $\mathrm{T}_{\mathrm{A}}$ | 0 | 25 | 70 | ${ }^{\circ} \mathrm{C}$ |
| Wave Shaping Resistor | $\mathrm{R}_{\mathrm{WS}}$ | 10 | - | 1000 | $\mathrm{k} \Omega$ |

TARGET ELECTRICAL CHARACTERISTICS (Unless otherwise noted, specifications apply over recommended operating conditions)

| Characteristic | Symbol | Min | Typ | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
| Input Voltage - Low Logic State | $\mathrm{V}_{\text {IL }}$ | - | - | 0.8 | V |
| Input Voltage - High Logic State | $\mathrm{V}_{\mathrm{IH}}$ | 2.0 | - | - | V |
| Input Current - Low Logic State ( $\mathrm{V}_{\text {IL }}=0.4 \mathrm{~V}$ ) | ILL | -80 | - | - | $\mu \mathrm{A}$ |
| $\begin{aligned} & \text { Input Current - High Logic State } \\ & \left(\mathrm{V}_{1 H}=2.4 \mathrm{~V}\right) \\ & \left(\mathrm{V}_{1 H}=5.5 \mathrm{~V}\right) \end{aligned}$ | $\begin{aligned} & l_{\mid H 1} \\ & l_{1 H 2} \end{aligned}$ |  |  | $\begin{gathered} 10 \\ 100 \end{gathered}$ | $\mu \mathrm{A}$ |
| Input Clamp Diode Voltage ( $\mathrm{I}_{\mathrm{K}}=-15 \mathrm{~mA}$ ) | $\mathrm{V}_{\mathrm{IK}}$ | - 1.5 | - | - | V |
| $\begin{aligned} & \text { Output Voltage - Low Logic State } \\ & \left(R_{L}=\infty\right), \text { EIA-423 } \\ & \left(R_{L}=3.0 \mathrm{k} \Omega\right), \text { EIA-232D } \\ & \left(R_{L}=450 \Omega\right) \text {, EIA-423 } \end{aligned}$ | $\mathrm{V}_{\mathrm{OL}}$ | $\begin{aligned} & -6.0 \\ & -6.0 \\ & -6.0 \end{aligned}$ | - | $\begin{aligned} & -5.0 \\ & -5.0 \\ & -4.0 \end{aligned}$ | V |
| $\begin{gathered} \hline \text { Output Voltage - High Logic State } \\ \left(R_{L}=\infty\right), \text { EIA-423 } \\ \left(R_{L}=3.0 \mathrm{k} \Omega\right), \text { EIA-232D } \\ \left(R_{L}=450 \Omega\right), \text { EIA-423 } \end{gathered}$ | $\mathrm{V}_{\mathrm{OH}}$ | $\begin{aligned} & 5.0 \\ & 5.0 \\ & 4.0 \end{aligned}$ | - | $\begin{aligned} & 6.0 \\ & 6.0 \\ & 6.0 \end{aligned}$ | V |
| Output Resistance ( $\mathrm{R}_{\mathrm{L}} \geqslant 450 \Omega$ ) | $\mathrm{R}_{\mathrm{O}}$ | - | 25 | 50 | $\Omega$ |
| Output Short-Circuit Current (Note 2) $\left.\begin{array}{l} \left(V_{\text {in }}=V_{\text {out }}=0 \mathrm{~V}\right) \\ \left(V_{\text {in }}=V_{\text {IH }}(\text { Min) }\right. \end{array}, V_{\text {out }}=0 \mathrm{~V}\right) .$ | losh losL | $\begin{aligned} & -150 \\ & +15 \end{aligned}$ | - | $\begin{array}{r} -15 \\ +150 \end{array}$ | mA |
| Output Leakage Current (Note 3) ( $\left.\mathrm{V}_{\mathrm{CC}}=\mathrm{V}_{\mathrm{EE}}=0 \mathrm{~V},-6.0 \mathrm{~V} \leqslant \mathrm{~V}_{\mathrm{O}} \leqslant 6.0 \mathrm{~V}\right)$ | $\mathrm{l}_{\text {ox }}$ | - 100 | - | 100 | $\mu \mathrm{A}$ |
| Power Supply Currents ( $\left.\mathrm{R}_{\mathrm{W}}=100 \mathrm{k} \Omega, \mathrm{R}_{\mathrm{L}}=\infty, \mathrm{V}_{\mathrm{IL}} \leqslant \mathrm{V}_{\text {in }} \leqslant \mathrm{V}_{\mathrm{IH}}\right)$ | $\begin{aligned} & \mathrm{I}_{\mathrm{CC}} \\ & \mathrm{I}_{\mathrm{EE}} \end{aligned}$ | $-\overline{18}$ | - | $+18$ | mA |

2. One output shorted at a time.
3. No $V_{E E}$ diode required.

TRANSITION TIMES (Unless otherwise noted, $\mathrm{C}_{\mathrm{L}}=30 \mathrm{pF}, \mathrm{f}=1.0 \mathrm{kHz}, \mathrm{V}_{\mathrm{CC}}=-\mathrm{V}_{\mathrm{EE}}=12.0 \mathrm{~V} \pm 10 \%, \mathrm{~T}_{\mathrm{A}}=25^{\circ} \mathrm{C}, \mathrm{R}_{\mathrm{L}}=450 \Omega$.
Transition times measured $10 \%$ to $90 \%$ and $90 \%$ to $10 \%$ )

| Characteristic |  | Symbol | Min | Typ | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Transition Time, Low-to-High State Output |  | $\mathrm{t}_{\text {the }}$ |  |  |  | $\mu \mathrm{s}$ |
|  | $(\mathrm{Rw}=10 \mathrm{k} \Omega$ ) |  | 0.8 |  | 1.4 |  |
|  | ( $\mathrm{RW}_{\mathrm{W}}=100 \mathrm{k} \Omega$ ) |  | 8.0 |  | 14 |  |
|  | ( $\mathrm{R}_{\mathrm{W}}=500 \mathrm{k} \Omega$ ) |  | 40 |  | 70 |  |
|  | $\left(\mathrm{R}_{\mathrm{W}}=1000 \mathrm{k} \Omega\right)$ |  | 80 |  | 140 |  |
| Transition Time, High-to-Low State Output |  | ${ }_{\text {t }}^{\text {THL }}$ |  |  |  | $\mu \mathrm{s}$ |
|  |  |  |  |  |  |  |
|  | $\begin{aligned} & \left(R_{W}=100 \mathrm{k} \Omega\right) \\ & \left(\mathrm{R}_{\mathrm{W}}=500 \mathrm{k} \Omega\right) \end{aligned}$ |  | 8.0 40 |  | 14 70 |  |
|  | $\left(R_{W}=500 \mathrm{k} \Omega\right)$ $\left(\mathrm{R}_{\mathrm{W}}=1000 \mathrm{k} \Omega\right)$ |  | 80 |  | 140 |  |

ORDERING INFORMATION

| Device | Operating Temperature Range | Package | Shipping ${ }^{\dagger}$ |
| :---: | :---: | :---: | :---: |
| MC3488AD | $\mathrm{T}_{\mathrm{A}}=0$ to $+70^{\circ} \mathrm{C}$ | SOIC-8 | 98 Units / Rail |
| MC3488ADG |  | $\begin{gathered} \hline \text { SOIC-8 } \\ \text { (Pb-Free) } \end{gathered}$ | 98 Units / Rail |
| MC3488ADR2 |  | SOIC-8 | 1000 / Tape \& Reel |
| MC3488ADR2G |  | $\begin{gathered} \text { SOIC-8 } \\ \text { (Pb-Free) } \end{gathered}$ | 1000 / Tape \& Reel |
| MC3488AP1 |  | PDIP-8 | 50 Units / Rail |
| MC3488AP1G |  | $\begin{gathered} \text { PDIP-8 } \\ \text { (Pb-Free) } \end{gathered}$ | 50 Units / Rail |

$\dagger$ For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.


Figure 2. Test Circuit and Waveforms for Transition Times


Figure 3. Output Transition Times versus Wave Shape Resistor Value


Figure 4. Input/Output Characteristics versus Temperature


Figure 5. Output Current versus Output Voltage


Figure 6. Supply Current versus Temperature


Figure 7. Rise/Fall Time versus R $_{\text {Ws }}$


SCALE 1:1


$$
\begin{aligned}
& \text { STYLE 1: } \\
& \text { PIN 1. AC IN } \\
& \text { 2. DC }+ \text { IN } \\
& \text { 3. DC }- \text { IN } \\
& \text { 4. AC IN } \\
& \text { 5. GROUND } \\
& \text { 6. OUTPUT } \\
& \text { 7. AUXILIARY } \\
& \text { 8. VCC }
\end{aligned}
$$

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| DESCRIPTION: | PDIP-8 | PAGE 1 OF 1 |

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SOIC-8 NB
CASE 751-07
ISSUE AK
SCALE 1:1
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
. CONTROLLING DIMENSION: MILLIMETER.
2. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
3. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
4. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
5. 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

| DIM | MILLIMETERS |  | INCHES |  |
| :---: | :---: | :---: | :---: | :---: |
|  | MIN | MAX | MIN | MAX |
|  | 4.80 | 5.00 | 0.189 | 0.197 |
| B | 3.80 | 4.00 | 0.150 | 0.157 |
| C | 1.35 | 1.75 | 0.053 | 0.069 |
| D | 0.33 | 0.51 | 0.013 | 0.020 |
| G | 1.27 BSC |  | 0.050 BSC |  |
| H | 0.10 | 0.25 | 0.004 | 0.010 |
| J | 0.19 | 0.25 | 0.007 | 0.010 |
| K | 0.40 | 1.27 | 0.016 | 0.050 |
| M | 0 | $\circ$ | $8^{\circ}$ | 0 |
|  | $\circ$ | 8 |  |  |
| N | 0.25 | 0.50 | 0.010 | 0.020 |
| S | 5.80 | 6.20 | 0.228 | 0.244 |

GENERIC
MARKING DIAGRAM*



XXXXX = Specific Device Code
A = Assembly Location
L Wafer Lot
= Year
= Work Week
= Pb-Free Package
*This information is generic. Please refer to device data sheet for actual part marking. $\mathrm{Pb}-\mathrm{Free}$ indicator, " G " or microdot " $\mathrm{=}$ ", may or may not be present. Some products may not follow the Generic Marking.
*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

## STYLES ON PAGE 2

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CASE 751-07
ISSUE AK
DATE 16 FEB 2011

STYLE

| PIN 1. | EMITTER |
| ---: | :--- |
| 2. | COLLECTOR |
| 3. | COLLECTOR |
| 4. | EMITTER |
| 5. | EMITTER |
| 6. | BASE |
| 7. | BASE |
| 8. | EMITTER |
| STYLE 5: |  |
| PIN 1. | DRAIN |
| 2. | DRAIN |
| 3. | DRAIN |
| 4. | DRAIN |
| 5. | GATE |
| 6. | GATE |
| 7. | SOURCE |
| 8. | SOURCE |

STYLE 9:
PIN 1. EMITTER, COMMON
COLLECTOR, DIE \#1 COLLECTOR, DIE \#2 EMITTER, COMMON EMITTER, COMMON BASE, DIE \#2
BASE, DIE \#1
8. EMITTER, COMMON

STYLE 13:
PIN 1. N.C.
2. SOURCE
3. SOURCE

GATE
DRAIN
DRAIN
DRAIN
8. DRAIN

STYLE 17:
PIN 1. VCC
2. V2OUT

V1OUT
TXE
RXE
VEE
7. GND
8. ACC

STYLE 21:
PIN 1. CATHODE 1
2. CATHODE 2
3. CATHODE 3

CATHODE 4
CATHODE 5
6. COMMON ANODE
7. COMMON ANODE
8. CATHODE 6

STYLE 25:
PIN 1. VIN
2. $N / C$

REXT
GND
IOUT
IOUT
IOUT
8. IOUT

## STYLE 29:

PIN 1. BASE, DIE \#
EMITTER, \#1
BASE, \#2
. EMITTER, \#2
5. COLLECTOR, \#2
6. COLLECTOR, \#2
7. COLLECTOR, \#1
7. COLLECTOR, \#1

STYLE
PIN 1. COLIECTOR, DIE,
2. COLLECTOR, \#1
3. COLLECTOR, \#2

COLLECTOR, \#2
BASE, \#2
. EMITTER, \#2
7. BASE, \#1
8. EMITTER, \#1

STYLE 6:
PIN 1. SOURCE
DRAIN
3. DRAIN
4. SOURCE

SOURCE
6. GATE
7. GATE
8. SOURCE

STYLE 10:
PIN 1. GROUND
2. BIAS 1
3. OUTPUT
4. GROUND

GROUND
BIAS 2
7. INPUT
8. GROUND

STYLE 14:
PIN 1. N-SOURCE
2. N-GATE

P-SOURCE
P-GATE
5.DRAIN
6. P-DRAIN
7. N-DRAIN
8. N -DRAIN

STYLE 18
PIN 1. ANODE
2. ANODE
3. SOURCE
4. GATE
5. DRAIN
6. DRAIN
7. CATHODE
8. CATHODE

STYLE 22 :
PIN 1. I/O LINE
2. COMMON CATHODE/VCC
3. COMMON CATHODE/VCC
4. I/O LINE 3
5. COMMON ANODE/GND
6. I/O LINE 4
7. I/O LINE 5
8. COMMON ANODE/GND

STYLE 26:
PIN 1. GND
2. $\mathrm{dv} / \mathrm{dt}$
3. ENABLE
4. ILIMIT
5. SOURCE

SOURCE
7. SOURCE
8. VCC

STYLE 30:
PIN 1. DRAIN 1
2. DRAIN 1
. GATE 2
4. SOURCE 2
5. SOURCE 1/DRAIN 2
. SOURCE 1/DRAIN 2
SOURCE 1/DRAIN 2
8. GATE 1

STYLE 3
STYLE

1. DRAIN, DIE
2. DRAIN, \#1
3. DRAIN, \#
4. DRAIN, \#2
5. DRAIN, \#2
6. GATE, \#2
7. GATE, \#1
8. SOURCE, \#1

## STYLE 7

PIN 1. INPUT
2. EXTERNAL BYPASS
3. THIRD STAGE SOURCE
4. GROUND
5. DRAIN
6. GATE 3
7. SECOND STAGE Vd
8. FIRST STAGE Vd

## STYLE 11:

PIN 1. SOURCE
2. GATE 1
3. SOURCE 2
4. GATE 2
5. DRAIN 2
6. DRAIN 2
7. DRAIN
8. DRAIN 1

## STYLE 15:

PIN 1. ANODE 1
2. ANODE 1
3. ANODE 1
4. ANODE 1
5. CATHODE, COMMON
6. CATHODE, COMMON
7. CATHODE, COMMON
8. CATHODE, COMMON

## STYLE 19:

PIN 1. SOURCE
2. GATE 1
3. SOURCE 2
4. GATE 2
5. DRAIN
6. MIRROR 2
7. DRAIN 1
8. MIRROR 1

## STYLE 23:

PIN 1. LINE 1 IN
2. COMMON ANODE/GND
3. COMMON ANODE/GND
4. LINE 2 IN
5. LINE 2 OUT
6. COMMON ANODE/GND
7. COMMON ANODE/GND
8. LINE 1 OUT

STYLE 27:
PIN 1. ILIMIT
2. OVLO
3. UVLO
4. INPUT+
5. INPUT+
5. SOURCE
6. SOURCE
7. SOURCE
8. DRAIN

STYLE 4:
PIN 1. ANODE
2. ANODE
3. ANODE
4. ANODE
5. ANODE
6. ANODE
8. COMMON CATHODE

## STYLE 8:

PIN 1. COLLECTOR, DIE \#1
2. BASE, \#1
3. BASE, \#2
4. COLLECTOR, \#2
5. COLLECTOR, \#2
6. EMITTER, \#2
7. EMITTER, \#1
8. COLLECTOR, \#1

## STYLE 12

PIN 1. SOURCE
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN
6. DRAIN
7. DRAIN
8. DRAIN

## STYLE 16:

PIN 1. EMITTER, DIE \#1
2. BASE, DIE \#1
3. EMITTER, DIE \#2
3. EMITTER, DIE
4. BASE, DIE \#2
4. BASE, DIE \#2
6. COLLECTOR, DIE \#2
7. COLLECTOR, DIE \#1
8. COLLECTOR, DIE \#1

## STYLE 20:

PIN 1. SOURCE (N)
2. GATE (N)
3. SOURCE (P)
4. GATE (P)
5. DRAIN
6. DRAIN
7. DRAIN
8. DRAIN

STYLE 24
PIN 1. BASE
2. EMITTER
3. COLLECTOR/ANODE
4. COLLECTOR/ANODE
5. CATHODE
6. CATHODE
7. COLLECTOR/ANODE
8. COLLECTOR/ANODE

## STYLE 28:

PIN 1. SW_TO_GND
2. DA $\bar{S} I C \bar{O} F F$
3. DASIC_SW_DET
4. GND
5. V_MON
6. VBUULK
7. VBULK
8. VIN

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